



Correction to: Anisotropic Optoelectronic Properties of MAPbI₃ on (100), (112) and (001) Facets

Bo Chen¹ · Yuchen Bai¹ · Hong Tao¹ · Qiuming Fu¹ · Liwei Xiong¹ · Jun Weng¹ · Shenggao Wang¹ · Hongyang Zhao¹ · Yibo Han² · Jianxu Ding³

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In the Experimental Section, second paragraph of the original article, the crystals were completely stirred at 60°C. The original online version of the article was incorrect as it was stated as 6°C.

The original article was corrected.

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✉ Hongyang Zhao
zhaohy@wit.edu.cn

✉ Jianxu Ding
dingjianxu@sdust.edu.cn

¹ Hubei Key Laboratory of Plasma Chemistry and Advanced Materials, Wuhan Institute of Technology, No. 206 Guanggu 1st Road, Wuhan 430205, China

² Middle School Attached to Huazhong University of Science and Technology, Wuhan 430074, China

³ College of Materials Science and Engineering, Shandong University of Science and Technology, Qingdao 266590, China